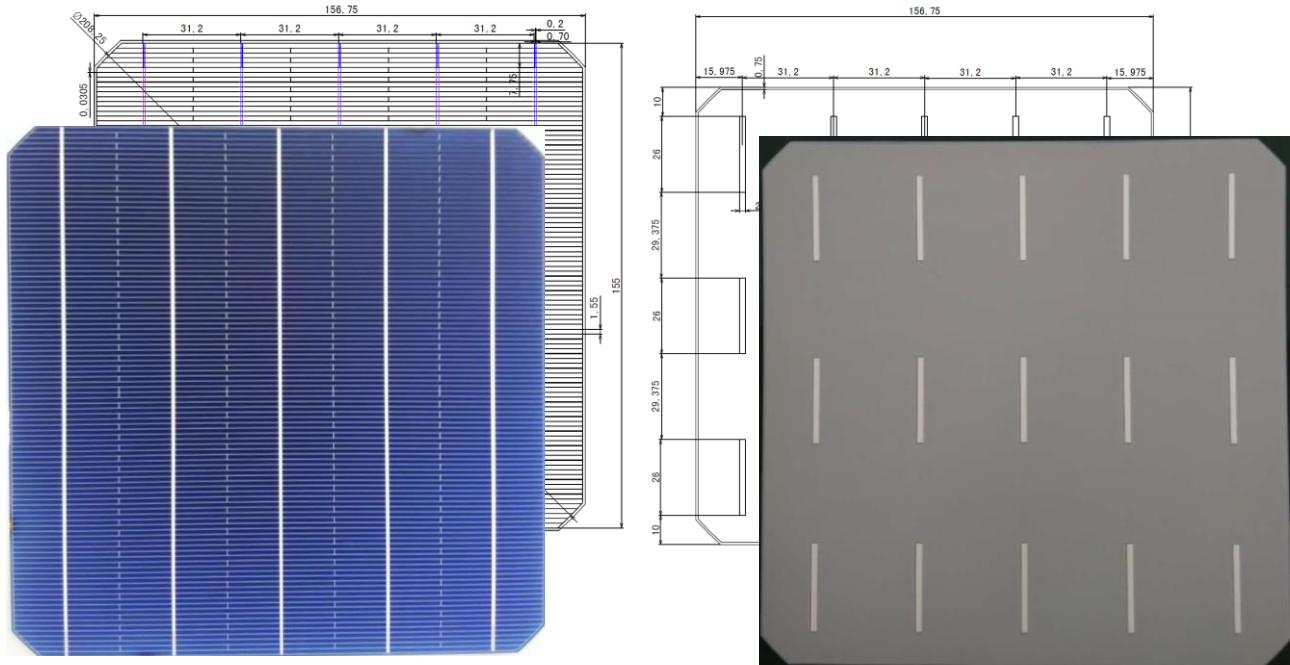


1 . Appearance:



2. Appearance Description:

Dimension: 156.75mm×156.75mm±0.25mm (Φ210±0.25mm)

Thickness (Si Wafer): 200μm±20μm

Front Side (-): Silicon oxide + blue silicon nitride compound anti-reflection coating (Ozone PID Free) ;0.7 mm silver bus bar , hollow both ends of bus bar ;bus bar parallel to the spine silver line

Back Side (+): Full surface aluminum back surface field, 3 sections 2.0mm silver anode.

3. Features:

Rigorous standards and finger design, effectively reducing the power loss in the module package.

Strict appearance standards, improve the passing rate of module production.

Unique cell structure designed to effectively reduce the module production breaking rate.

Lower reverse leakage, effectively improve the stability of the module.

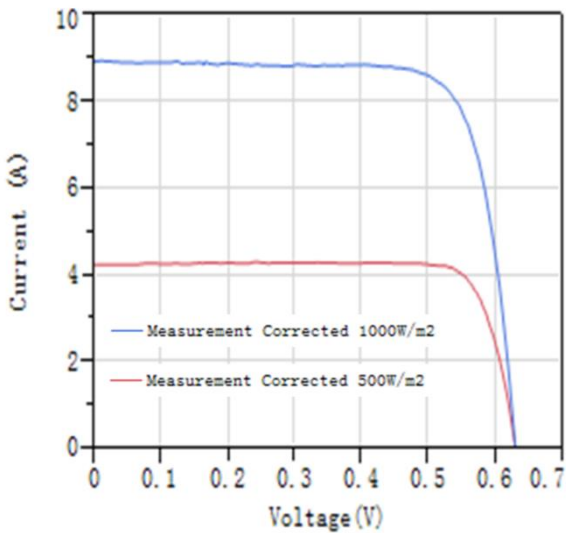
Strict pulling force test, to ensure a good weld ability.

Excellent anti-PID performance to ensure the stability of the module power.

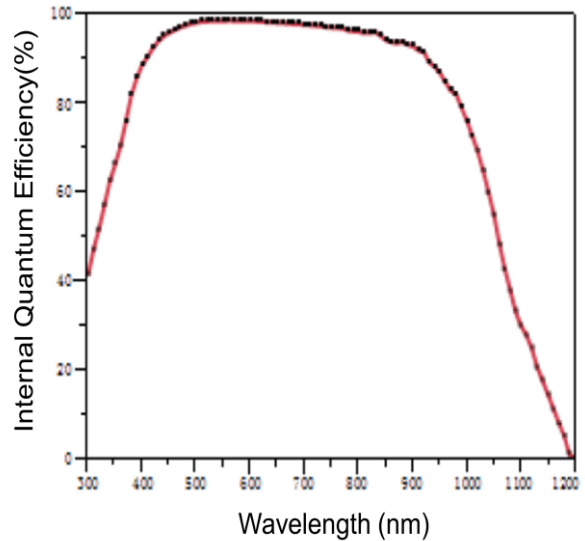
4. Electrical Characteristics:

Eff (%)	Pmpp (W)	Umpp(V)	Impp(A)	Voc(V)	Isc(A)	FF(%)
20.4-20.5	4.98	0.555	8.982	0.649	9.480	81.00
20.3-20.4	4.96	0.553	8.969	0.648	9.450	80.96
20.2-20.3	4.94	0.551	8.963	0.646	9.448	80.91
20.1-20.2	4.91	0.549	8.939	0.644	9.445	80.77
20.0-20.1	4.89	0.548	8.929	0.642	9.436	80.72
19.9-20.0	4.86	0.547	8.899	0.641	9.412	80.69
19.8-19.9	4.84	0.546	8.857	0.641	9.393	80.41
19.7-19.8	4.81	0.544	8.839	0.639	9.379	80.30
19.6-19.7	4.79	0.543	8.822	0.638	9.362	80.27
19.5-19.6	4.76	0.541	8.798	0.637	9.351	79.91
19.4-19.5	4.74	0.540	8.787	0.636	9.338	79.80
19.3-19.4	4.72	0.539	8.761	0.636	9.325	79.67

5. IV-Curve:



6. Spectral Response:



7. Temperature coefficients:

TkVoltage(mV/K) : -0.33

TkCurrent(mA/K) : 0.04

TkPower(%/K) : -0.38

8. Light Intensity Dependence :

Intensity (W/m ²)	Vmpp	Impp
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1000	1.000	1.000
800	0.990	0.801
600	0.977	0.600
200	0.923	0.195

Ratio of V_{mpp} (I_{mpp}) at reduced intensity to V_{mpp} (I_{mpp}) at 1000 (W/m^2)
